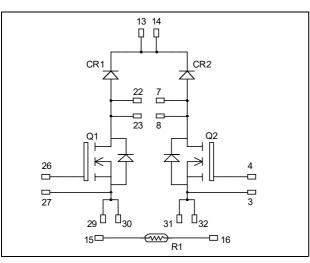
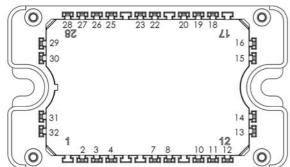


Dual Boost chopper <u>MOSFET Powe</u>r Module





All multiple inputs and outputs must be shorted together Example: 13/14 ; 29/30 ; 22/23 ...

APTM50DDAM65T3G

$V_{DSS} = 500V$

 $R_{DSon} = 65m\Omega typ$ @ $Tj = 25^{\circ}C$

 $I_D = 51A$ (a) $T_c = 25^{\circ}C$

Application

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction

Features

• Power MOS 7[®] MOSFETs

- Low R_{DSon}
 - Low input and Miller capacitance
 - Low gate charge
 - Avalanche energy rated
 - Very rugged
- Kelvin source for easy drive
- Very low stray inductance
- Internal thermistor for temperature monitoring

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- Each leg can be easily paralleled to achieve a single boost of twice the current capability
- RoHS Compliant

Absolute maximum ratings (per MOSFET)

Symbol	Parameter		Max ratings	Unit	
V _{DSS}	Drain - Source Voltage		500	V	
т	Continuous Drain Current	$T_c = 25^{\circ}C$	51		
I _D	Continuous Drain Current	$T_c = 80^{\circ}C$	38	А	
I _{DM}	Pulsed Drain current		204	1	
V _{GS}	Gate - Source Voltage		± 30	V	
R _{DSon}	Drain - Source ON Resistance		78	mΩ	
PD	Power Dissipation $T_c = 25^{\circ}C$		390	W	
I _{AR}	Avalanche current (repetitive and non repetitive)		51	А	
E _{AR}	Repetitive Avalanche Energy		50	m I	
E _{AS}	Single Pulse Avalanche Energy		3000	mJ	

These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

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All ratings (a) $T_i = 25^{\circ}C$ unless otherwise specified

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Electrical Characteristics (per MOSFET)

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
I _{DSS}	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 500V$			100	μΑ
R _{DS(on)}	Drain – Source on Resistance	$V_{GS} = 10V, I_D = 25.5A$		65	78	mΩ
V _{GS(th)}	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 2.5 \text{mA}$	3		5	V
I _{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$			±150	nA

Dynamic Characteristics (per MOSFET)

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
C _{iss}	Input Capacitance	$V_{GS} = 0V$		7000		
Coss	Output Capacitance	$V_{\rm DS} = 25 V$		1400		pF
Crss	Reverse Transfer Capacitance	f=1MHz		90		
Qg	Total gate Charge	$V_{GS} = 10V$		140		
Q_{gs}	Gate – Source Charge	$V_{Bus} = 250V$		40		nC
Q_{gd}	Gate – Drain Charge	$I_D = 51A$		70		
T _{d(on)}	Turn-on Delay Time	Inductive switching @ 125°C		21		
Tr	Rise Time	$V_{GS} = 15V$		38		ns
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 333V$ $I_D = 51A$		75		
$T_{\rm f}$	Fall Time	$R_G = 3\Omega$		93		
Eon	Turn-on Switching Energy	Inductive switching @ 25°C $V_{GS} = 15V, V_{Bus} = 333V$ $I_D = 51A, R_G = 3\Omega$		1035		T
E_{off}	Turn-off Switching Energy			845		μĴ
Eon	Turn-on Switching Energy	$- \frac{\text{Inductive switching (a) 125°C}}{V_{GS} = 15V, V_{Bus} = 333V}$ $I_D = 51A, R_G = 3\Omega$		1556		T
E_{off}	Turn-off Switching Energy			1013		μJ
R_{thJC}	Junction to Case Thermal Resistar	nce			0.32	°C/W

Chopper Diode ratings and characteristics (per diode)

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
V _{RRM}	Peak Repetitive Reverse Voltage					600	V
I _{RM}	Reverse Leakage Current	V _R =600V				350	μA
$I_{\rm F}$	DC Forward Current		$T_c = 40^{\circ}C$		80		А
V	Diode Forward Voltage	$I_F = 80A$	$T_j = 25^{\circ}C$		1.45		V
V_{F}			$T_j = 125^{\circ}C$		1.35		v
t	Reverse Recovery Time	$I_{\rm F} = 80A$ $V_{\rm R} = 300V$ $T_{\rm j} = 0$ $T_{\rm j} = 0$	$T_j = 25^{\circ}C$		95		na
t _{rr}	Reverse Recovery Time		$T_j = 125^{\circ}C$		115		ns
0			$T_j = 25^{\circ}C$		5.2		чC
Q _{rr}			$T_j = 125^{\circ}C$		8		μC
R_{thJC}	Junction to Case Thermal Resistance					0.8	°C/W

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Thermal and package characteristics

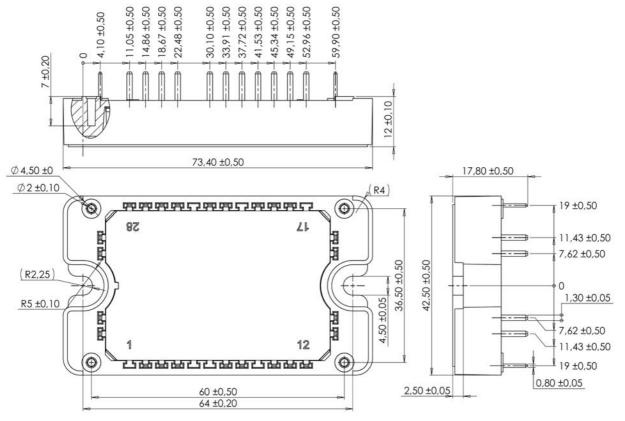
Symbol	Characteristic			Min	Max	Unit		
VISOL	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000		V		
TJ	Operating junction temperature range			-40	150			
T _{JOP}	Recommended junction temperature under switching conditions			-40	T _J max - 25	°C		
T _{STG}	Storage Temperature Range			-40	125	C		
T _C	Operating Case Temperature			-40	125			
Torque	Mounting torque	To heatsink	M4	2	3	N.m		
Wt	Package Weight				110	g		

Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic		Min	Тур	Max	Unit
R ₂₅	Resistance @ 25°C			50		kΩ
$\Delta R_{25}/R_{25}$				5		%
B _{25/85}	$T_{25} = 298.15 \text{ K}$			3952		Κ
$\Delta B/B$		$T_C=100^{\circ}C$		4		%

$$R_{T} = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$
 T: Thermistor temperature
R_T: Thermistor value at T

Package outline (dimensions in mm)



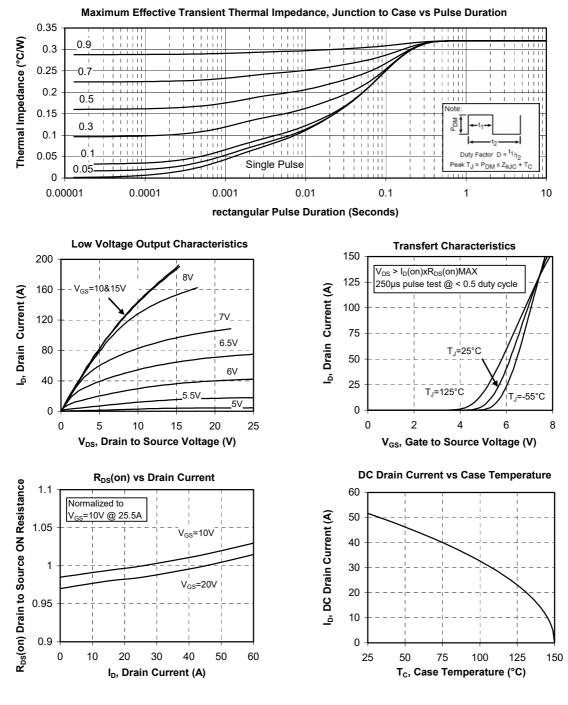
See application note 1906 - Mounting Instructions for SP3F Power Modules on www.microsemi.com

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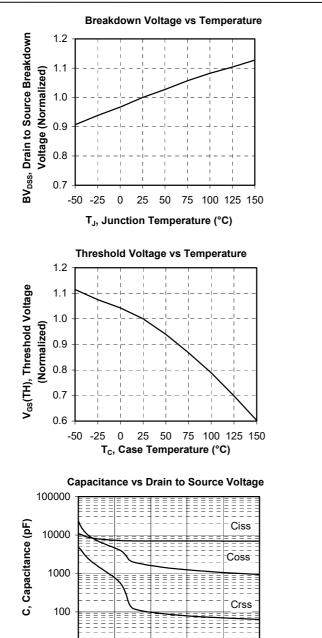
Typical Performance Curve



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10

0

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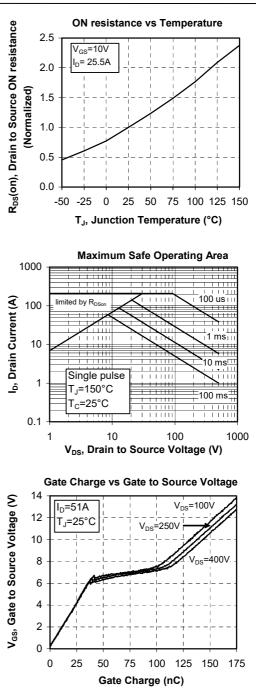
V_{DS}, Drain to Source Voltage (V)

30

40

50

APTM50DDAM65T3G





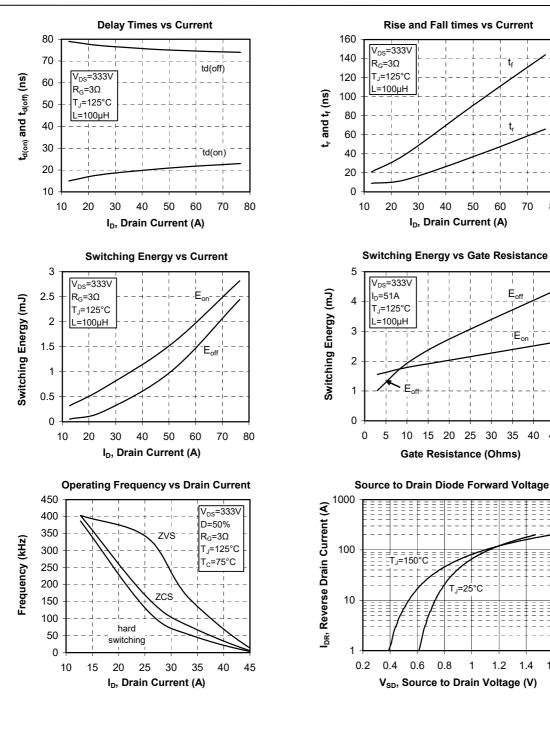
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80

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